

Single N-channel MOSFET

ELM4N6032FDA-N

<https://www.elm-tech.com>

■General description

ELM4N6032FDA-N uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate threshold voltage.

■Features

- $V_{ds}=60V$
- $I_d=75A$ ($V_{gs}=10V$)
- $R_{ds(on)} = 8.5m\Omega$ ($V_{gs}=10V$)
- $R_{ds(on)} = 12.0m\Omega$ ($V_{gs}=4.5V$)

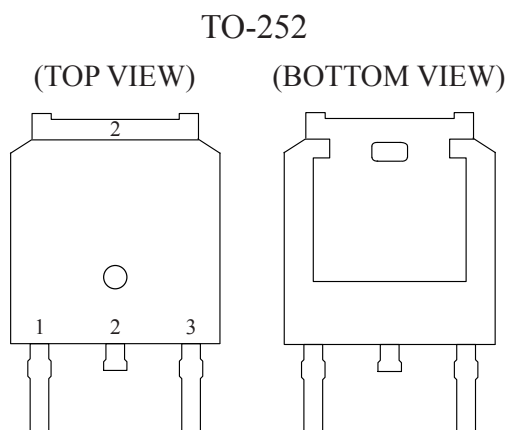
■Maximum absolute ratings

Parameter		Symbol	Limit	Unit	Note
Drain-source voltage		V_{ds}	60	V	
Gate-source voltage		V_{gs}	± 20	V	
Continuous drain current ($V_{gs}=10V$)	$T_c=25^{\circ}C$	I_d	75	A	1
	$T_c=100^{\circ}C$		47		
Pulsed drain current		I_{dm}	280	A	2
Single pulsed avalanche energy		E_{as}	80	mJ	3
Avalanche current		I_{as}	40	A	
Total power dissipation	$T_c=25^{\circ}C$	P_d	41	W	4
Storage temperature range		T_{stg}	-55 to 150	$^{\circ}C$	
Operating junction temperature range		T_j	-55 to 150	$^{\circ}C$	

■Thermal characteristics

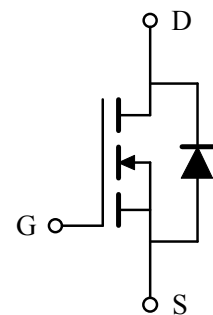
Parameter	Symbol	Typ.	Max.	Unit	Note
Thermal resistance junction-ambient	$R_{\theta ja}$	-	62.0	$^{\circ}C/W$	1
Thermal resistance junction-case	$R_{\theta jc}$	-	1.4		

■Pin configuration



Pin No.	Pin name
1	GATE
2	DRAIN
3	SOURCE

■Circuit



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■Electrical characteristics

Tj=25°C. Unless otherwise noted.

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BVdss	Vgs=0V, Id=250μA	60	-	-	V	
Static drain-source on-resistance	Rds(on)	Vgs=10V, Id=20A	-	7.1	8.5	mΩ	2
		Vgs=4.5V, Id=15A	-	9.5	12.0		
Gate threshold voltage	Vgs(th)	Vgs=Vds, Id=250μA	1.2	-	2.5	V	
Drain-source leakage current	Idss	Vds=48V, Vgs=0V	-	-	1	μA	
		Vds=48V, Vgs=0V, Tj=55°C	-	-	5		
Gate-source leakage current	Igss	Vgs=±20V, Vds=0V	-	-	±100	nA	
Diode forward voltage	Vsd	Vgs=0V, Is=1A	-	-	1.2	V	2
Continuous source current	Is	Vgs=Vds=0V, Force current	-	-	75	A	1, 5
Diode forward voltage	Vsd	Vgs=0V, Is=1A	-	-	1.2	V	2
DYNAMIC PARAMETERS							
Input capacitance	Ciss	Vds=30V, Vgs=0V, f=1MHz	-	3307	-	pF	
Output capacitance	Coss		-	201	-	pF	
Reverse transfer capacitance	Crss		-	151	-	pF	
Gate resistance	Rg	Vds=0V, Vgs=0V, f=1MHz	-	1.2	-	Ω	
SWITCHING PARAMETERS							
Total gate charge (10V)	Qg	Vds=30V, Vgs=10V Id=18A	-	57.0	-	nC	
Gate-source charge	Qgs		-	8.7	-	nC	
Gate-drain charge	Qgd		-	14.0	-	nC	
Turn-on delay time	td(on)	Vdd=30V, Vgs=10V Rgen=3.3Ω, Id=20A	-	16.2	-	ns	
Turn-on rise time	tr		-	41.2	-	ns	
Turn-off delay time	td(off)		-	56.4	-	ns	
Turn-off fall time	tf		-	16.2	-	ns	
Reverse recovery time	trr	If=20A, di/dt=100A/μs	-	22	-	nS	
Reverse recovery charge	Qrr		-	72	-	nC	

NOTE :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300μs and duty cycle ≤ 2%.
3. The Eas data shows Max. rating . The test condition is Vdd=50V, Vgs=10V, L=0.1mH, Ias=40A.
4. The power dissipation is limited by 150°C junction temperature.
5. The data is theoretically the same as Id and Idm, in real applications, should be limited by total power dissipation.

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■ Typical characteristics

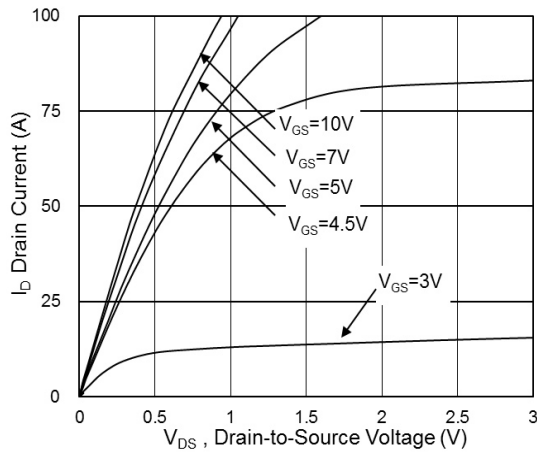


Fig.1 Typical Output Characteristics

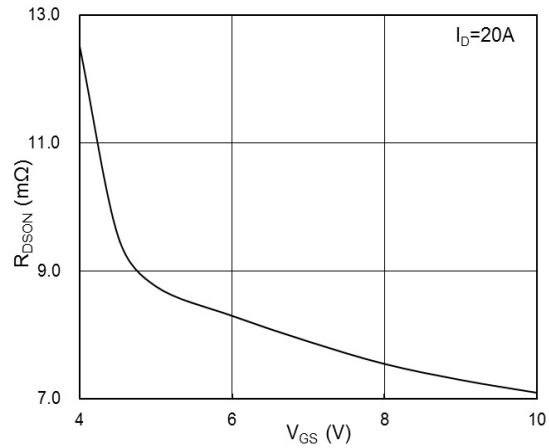


Fig.2 On-Resistance vs Gate-Source Voltage

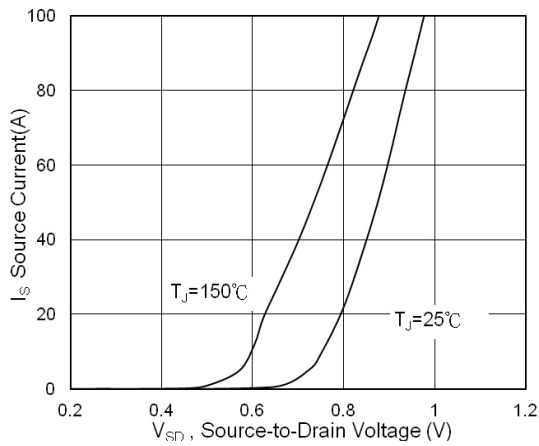


Fig.3 Forward Characteristics of Reverse

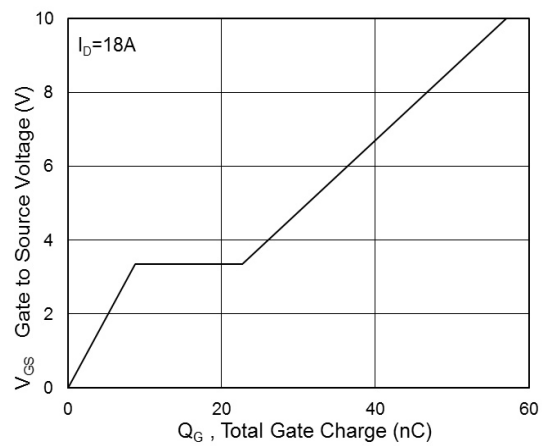


Fig.4 Gate-Charge Characteristics

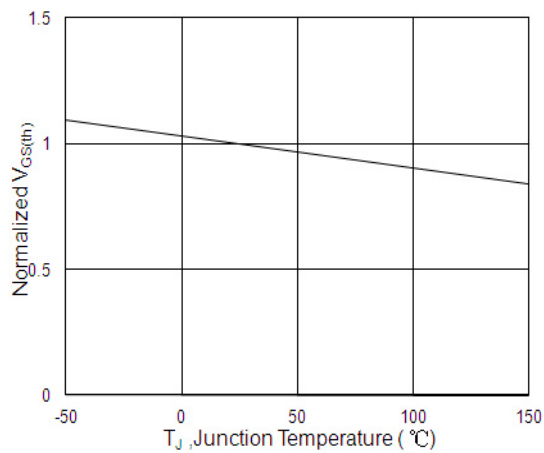


Fig.5 Normalized $V_{GS(th)}$ vs T_J

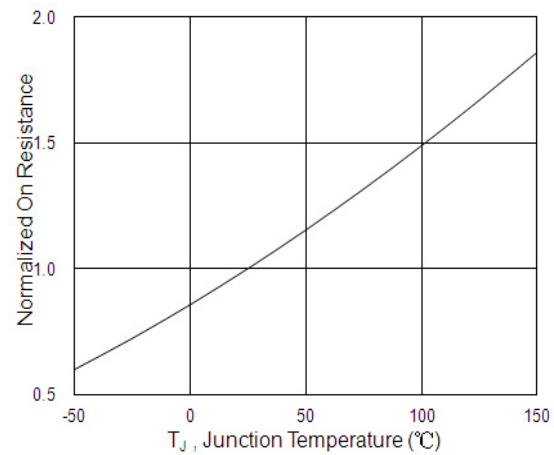


Fig.6 Normalized $R_{DS(on)}$ vs T_J

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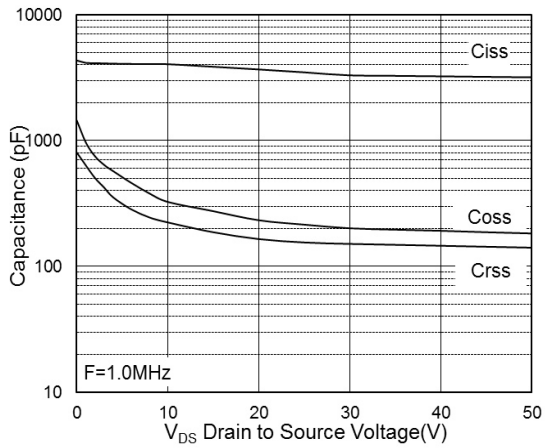


Fig.7 Capacitance

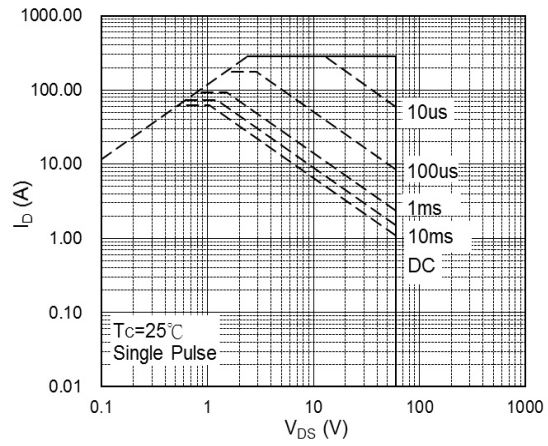


Fig.8 Safe Operating Area

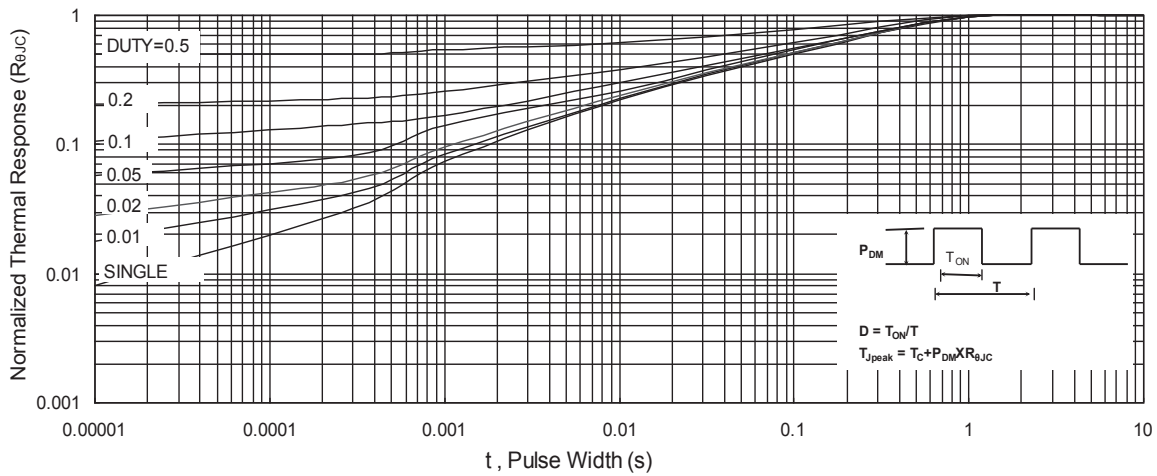


Fig.9 Normalized Maximum Transient Thermal Impedance

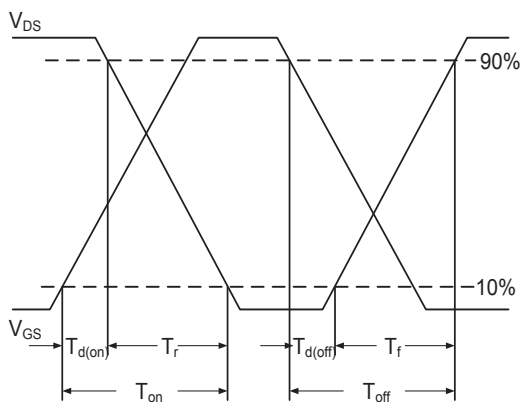


Fig.10 Switching Time Waveform

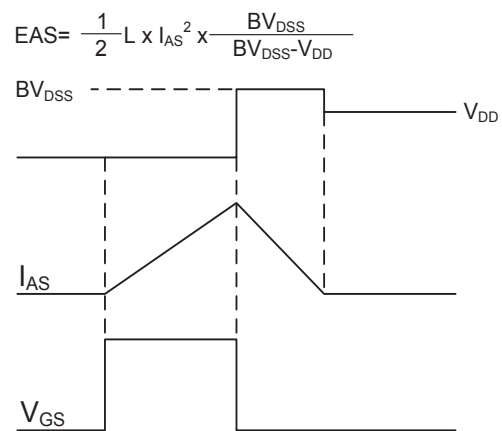


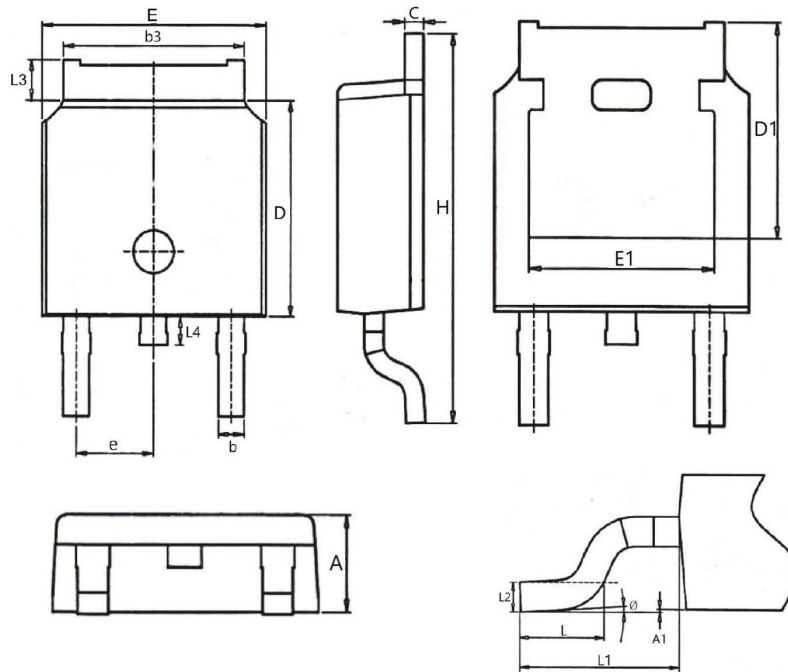
Fig.11 Unclamped Inductive Switching Waveform

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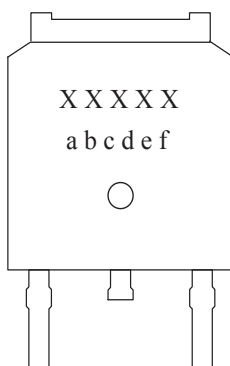
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■TO-252 dimension (2,500pcs/reel)



Symbols	Millimeters		Inches		Symbols	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	2.18	2.40	0.086	0.095	e	2.286BSC		0.09BSC	
A1	---	0.20	---	0.008	H	9.40	10.50	0.370	0.413
b	0.68	0.90	0.026	0.036	L	1.38	1.78	0.054	0.070
b3	4.95	5.46	0.194	0.215	L1	2.90REF		0.114REF	
c	0.43	0.89	0.017	0.035	L2	0.51BSC		0.020BSC	
D	5.97	6.22	0.235	0.245	L3	0.88	1.28	0.034	0.050
D1	5.300REF		0.209REF		L4	0.50	1.00	0.019	0.039
E	6.35	6.73	0.250	0.265	θ	0°	8°	0°	8°
E1	4.32	---	0.170	---					

■Marking



Symbols	Content
xxxxxx	Product code
a	Yearly code: 2019=K, 2020=L, 2021=M...
b, c	Weekly code: 01 to 53
d, e	Sequence: 01 to 99 or 0A to 0Z
f	Assembly code: A to Z (I, O excepted)